NSN 5961-00-061-3208

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Inclosure Material: Metal **Overall Length:** 0.505 inches **Overall Diameter:** 0.453 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.650 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 200.0 breakover voltage, dc **Current Rating Per Characteristic:** 16.00 amperes source cutoff current **Power Rating Per Characteristic:** 1.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 120.0 degrees celsius junction **Special Features:** Internal junction configuration arrangement pnpn **Thread Series Designator:** Unf **Terminal Type And Quantity:** 2 tab, solder lug and 1 threaded stud **Specification Data:** 80131-release4957 professional/industrial association specification Shelf Life: N/a **Unit Of Measure:**

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Demilitarization:

No

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